

MOSFET Transistor, P Channel, 3.4 A, 40 V, 112 mohm, 10 V, -3 V Powe MOSFET

Manufacturers	Infineon Technologies Corporation
Package/Case	TSOP-6
Product Type	Transistors
RoHS	Green
Lifecycle	



Images are for reference only

Please submit RFQ for IRF5803TRPBF or [Email to us: sales@ovaga.com](mailto:sales@ovaga.com) We will contact you in 12 hours.

[RFQ](#)

General Description

These P-channel HEXFET® Power MOSFETs from International Rectifier utilize advanced processing techniques to achieve the extremely low on-resistance per silicon area. This benefit provides the designer with an extremely efficient device for use in battery and load management applications.

The TSOP-6 package with its customized leadframe produces a HEXFET® power MOSFET with RDS(on) 60% less than a similar size SOT-23. This package is ideal for applications where printed circuit board space is at a premium. Its unique thermal design and RDS(on) reduction enables a current-handling increase of nearly 300% compared to the SOT-23.

- Ultra Low On-Resistance
- P-Channel MOSFET
- Surface Mount
- Available in Tape & Reel
- Low Gate Charge

Features

RoHS Compliant

Low RDS(on)

Industry-leading quality

P-Channel MOSFET

Application

DC Switches

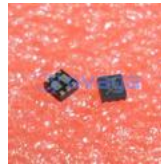
Load Switch

Related Products



[IRLTS6342TRPBF](#)

Infineon Technologies Corporation
TSOP-6



[IRLHS6376TRPBF](#)

Infineon Technologies Corporation
PQFN2x2DD



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